

Description

The MMBF170-F uses advanced trench technology

to provide excellent $R_{DS(ON)}$, low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

General Features

V_{DS} = 60V I_D =0.3A

 $R_{DS(ON)} < 2\Omega @ V_{GS}=10V$

ESD Rating: HBM≥2000V

Application

Battery protection

Load switch

Uninterruptible power supply

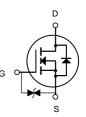
Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
MMBF170-F	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit	
Vds	Drain-Source Voltage		60	V
Vgs	Gate-Source Voltage		±20	V
	Continuous Drain Current (TJ =150℃)	T _A =25℃	0.3	
Ι _D		T _A =100 °C	0.19	A
Ідм	Drain Current-Pulsed (Note 1)		0.8	А
PD	Maximum Power Dissipation		0.35	W
Тј,Тѕтб	Operating Junction and Storage Temperature Range		-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)		350	°C /W





N-Channel MOSFET



Electrical Characteristics (T_A=25[°]Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	60	68	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	IGSS	V _{GS} =±10V,V _{DS} =0V V _{GS} =±20V,V _{DS} =0V	-	±100 ±4	±500 ±10	nA uA
Gate Threshold Voltage	VGS(th)	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.7	1.2	1.9	V
		V _{GS} =5V, I _D =0.1A	-	1.3	3	Ω
Drain-Source On-State Resistance	Rds(on)	V _{GS} =10V, I _D =0.1A	-	1	2	Ω
Forward Transconductance	g fs	V _{DS} =10V,I _D =0.2A	0.1	-	-	S
Input Capacitance	C _{lss}		-	21	50	PF
Output Capacitance	Coss	V _{DS} =25V,V _{GS} =0V, F=1.0MHz	-	11	25	PF
Reverse Transfer Capacitance	C _{rss}		-	4.2	5	PF
Turn-on Delay Time	td(on)		-	10	-	nS
Turn-on Rise Time	tr	V _{DD} =30V,I _D =0.2A	-	50	-	nS
Turn-Off Delay Time	td(off)	V_{GS} =10V,R _{GEN} =10Ω	-	17	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	V _{DS} =10V,I _D =0.3A, V _{GS} =4.5V	-	1.7	3	nC
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V,I _S =0.2A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	0.3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Electrical And Thermal Characteristics

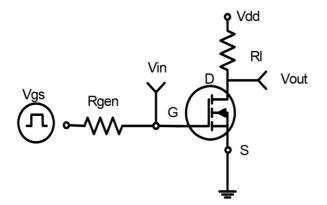
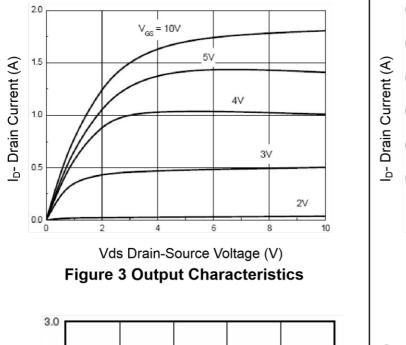
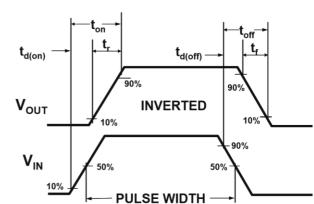


Figure 1:Switching Test Circuit







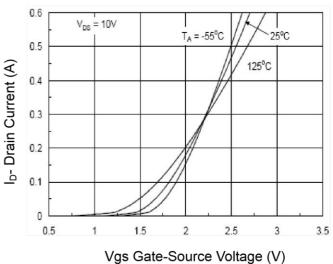
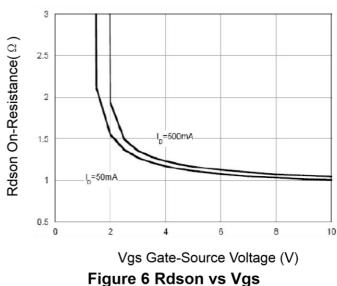


Figure 4 Transfer Characteristics



I_D- Drain Current (A) Figure 5 Drain-Source On-Resistance

0.6

0.4

V_{GS} = 10 V

0.8

1.0

 $V_{GS} = 5 V$

0.2

2.5

2.0

1.5

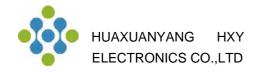
1.0

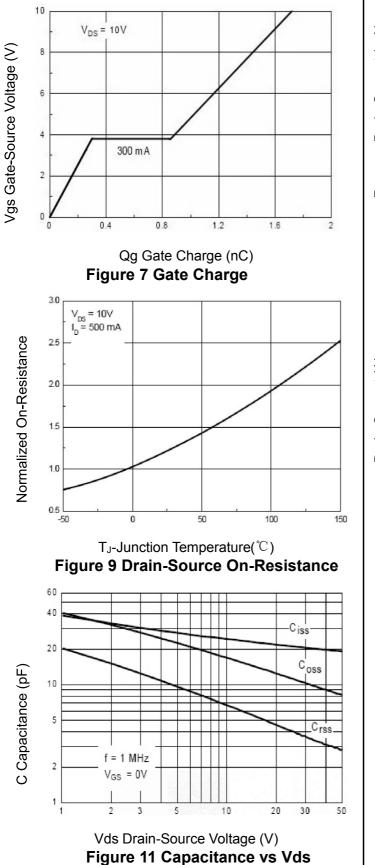
0.5

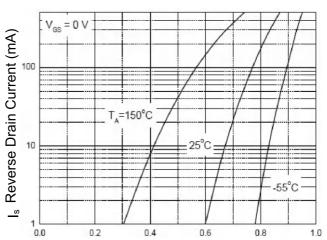
0.0

0.0

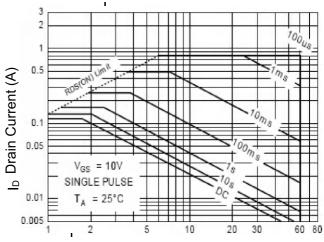
Rdson On-Resistance(Ω)







Vsd Source-Drain Voltage (V) Figure 8 Source-DrainDiode Forward



Vds Drain-Source Voltage (V) Figure 10 Safe Operation Area



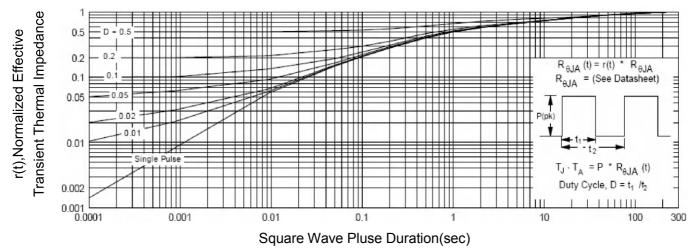
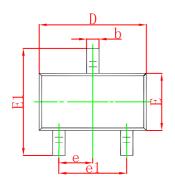
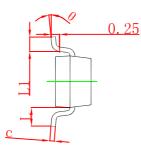


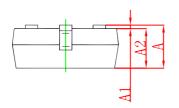
Figure 12 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

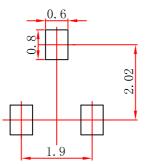






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
e	0.950)TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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